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With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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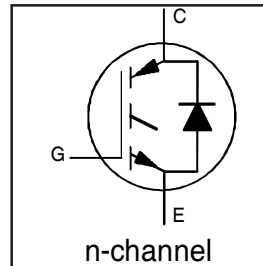
IRG4BC30KDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH
ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT

Features

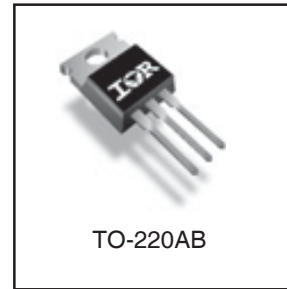
- High short circuit rating optimized for motor control, $t_{sc} = 10\mu s$, @360V V_{CE} (start), $T_J = 125^\circ C$, $V_{GE} = 15V$
- Combines low conduction losses with high switching speed
- tighter parameter distribution and higher efficiency than previous generations
- IGBT co-packaged with HEXFRED™ ultrafast, ultrasoft recovery antiparallel diodes
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on)}$ typ. = 2.21V
@ $V_{GE} = 15V, I_C = 16A$

Benefits

- Latest generation 4 IGBTs offer highest power density motor controls possible
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise, EMI and switching losses
- This part replaces the IRGBC30KD2 and IRGBC30MD2 products
- For hints see design tip 97003



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	28	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	16	
I_{CM}	Pulsed Collector Current ①	56	
I_{LM}	Clamped Inductive Load Current ②	56	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	12	
I_{FM}	Diode Maximum Forward Current	58	
t_{sc}	Short Circuit Withstand Time	10	μs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	100	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	42	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	---	---	1.2	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	---	---	2.5	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	---	0.50	---	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	---	---	80	
Wt	Weight	---	2 (0.07)	---	g (oz)

IRG4BC30KDPbF

International
IR Rectifier

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage ^③	600	—	—	V	V _{GE} = 0V, I _C = 250μA
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	0.54	—	V/°C	V _{GE} = 0V, I _C = 1.0mA
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	—	2.21	2.7	V	I _C = 16A V _{GE} = 15V
		—	2.88	—		I _C = 28A See Fig. 2, 5
		—	2.36	—		I _C = 16A, T _J = 150°C
V _{GE(th)}	Gate Threshold Voltage	3.0	—	6.0		V _{CE} = V _{GE} , I _C = 250μA
ΔV _{GE(th)} /ΔT _J	Temperature Coeff. of Threshold Voltage	—	-12	—	mV/°C	V _{CE} = V _{GE} , I _C = 250μA
g _{fe}	Forward Transconductance ^④	5.4	8.1	—	S	V _{CE} = 100V, I _C = 16A
I _{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	V _{GE} = 0V, V _{CE} = 600V
		—	—	2500		V _{GE} = 0V, V _{CE} = 600V, T _J = 150°C
V _{FM}	Diode Forward Voltage Drop	—	1.4	1.7	V	I _C = 12A See Fig. 13
		—	1.3	1.6		I _C = 12A, T _J = 150°C
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge (turn-on)	—	67	100	nC	I _C = 16A V _{CC} = 400V See Fig.8 V _{GE} = 15V
Q _{ge}	Gate - Emitter Charge (turn-on)	—	11	16		
Q _{gc}	Gate - Collector Charge (turn-on)	—	25	37		
t _{d(on)}	Turn-On Delay Time	—	60	—	ns	T _J = 25°C I _C = 16A, V _{CC} = 480V V _{GE} = 15V, R _G = 23Ω
t _r	Rise Time	—	42	—		
t _{d(off)}	Turn-Off Delay Time	—	160	250		
t _f	Fall Time	—	80	120		
E _{on}	Turn-On Switching Loss	—	0.60	—	mJ	Energy losses include "tail" and diode reverse recovery See Fig. 9,10,14
E _{off}	Turn-Off Switching Loss	—	0.58	—		
E _{ts}	Total Switching Loss	—	1.18	1.6	μs	V _{CC} = 360V, T _J = 125°C V _{GE} = 15V, R _G = 10Ω, V _{CPK} < 500V
t _{sc}	Short Circuit Withstand Time	10	—	—		
t _{d(on)}	Turn-On Delay Time	—	58	—	ns	T _J = 150°C, See Fig. 11,14 I _C = 16A, V _{CC} = 480V V _{GE} = 15V, R _G = 23Ω
t _r	Rise Time	—	42	—		
t _{d(off)}	Turn-Off Delay Time	—	210	—		
t _f	Fall Time	—	160	—		
E _{ts}	Total Switching Loss	—	1.69	—	mJ	Energy losses include "tail" and diode reverse recovery
L _E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C _{ies}	Input Capacitance	—	920	—	pF	V _{GE} = 0V V _{CC} = 30V See Fig. 7 f = 1.0MHz
C _{oes}	Output Capacitance	—	110	—		
C _{res}	Reverse Transfer Capacitance	—	27	—		
t _{rr}	Diode Reverse Recovery Time	—	42	60	ns	T _J = 25°C See Fig. 14
		—	80	120		T _J = 125°C
I _{rr}	Diode Peak Reverse Recovery Current	—	3.5	6.0	A	T _J = 25°C See Fig. 15
		—	5.6	10		T _J = 125°C
Q _{rr}	Diode Reverse Recovery Charge	—	80	180	nC	T _J = 25°C See Fig. 16
		—	220	600		T _J = 125°C
di _{(rec)M} /dt	Diode Peak Rate of Fall of Recovery During t _b	—	180	—	A/μs	T _J = 25°C See Fig. 17
		—	160	—		T _J = 125°C

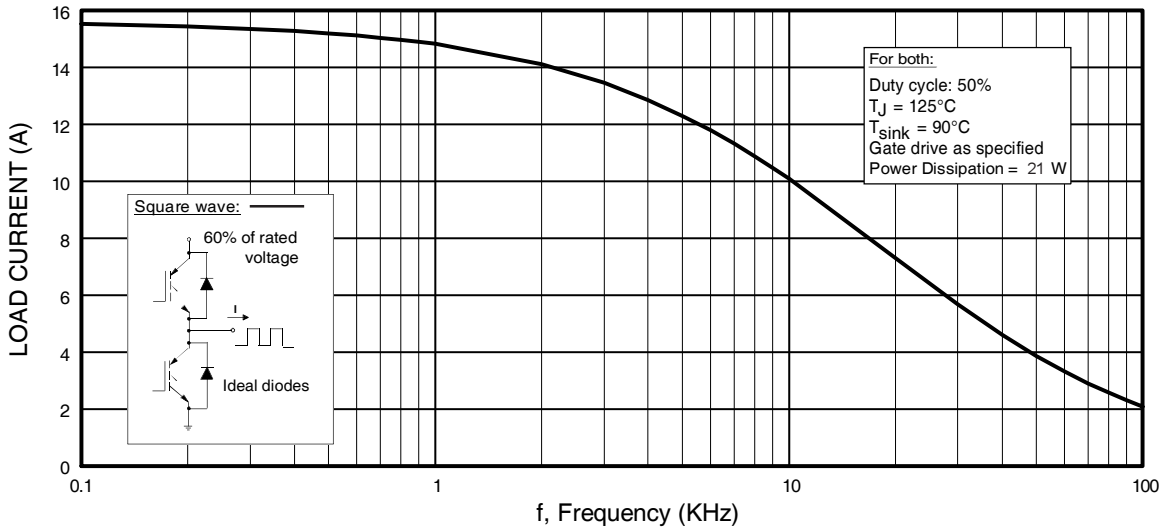


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

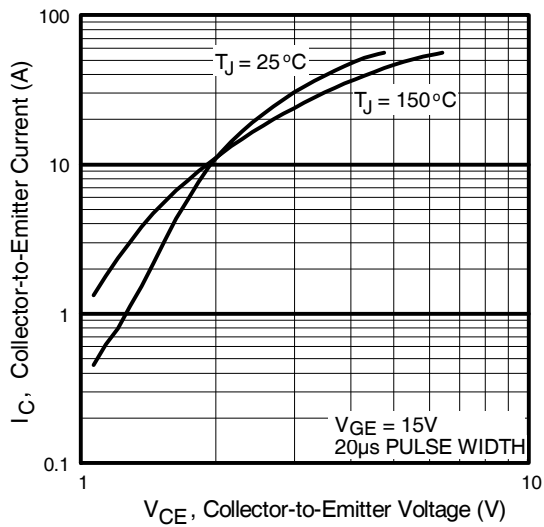


Fig. 2 - Typical Output Characteristics

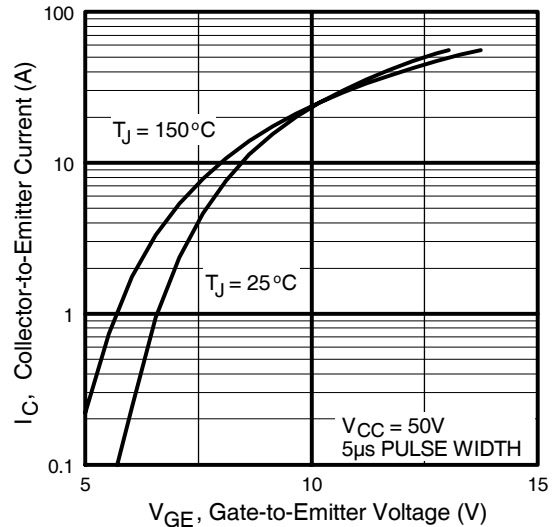


Fig. 3 - Typical Transfer Characteristics

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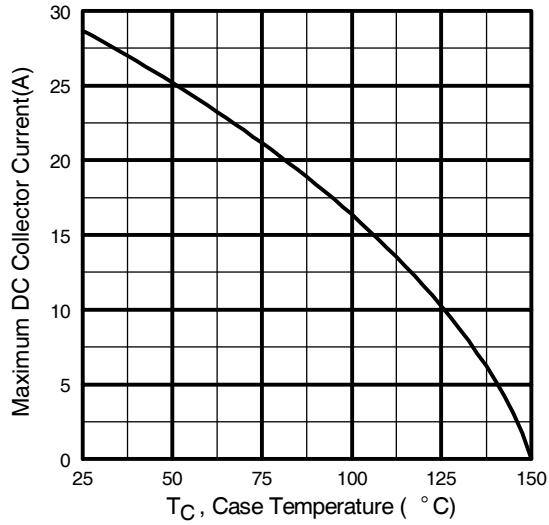


Fig. 4 - Maximum Collector Current vs. Case Temperature

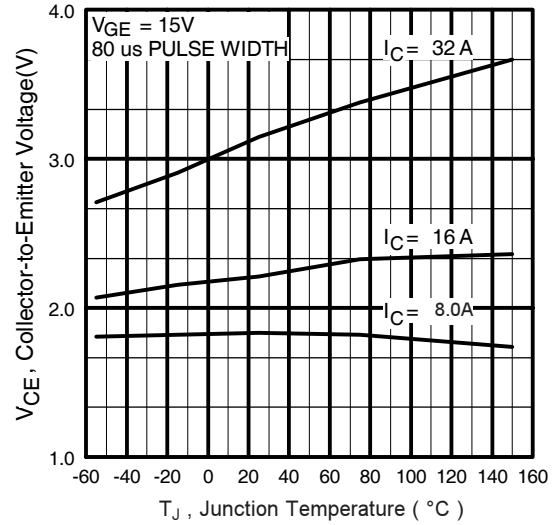


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

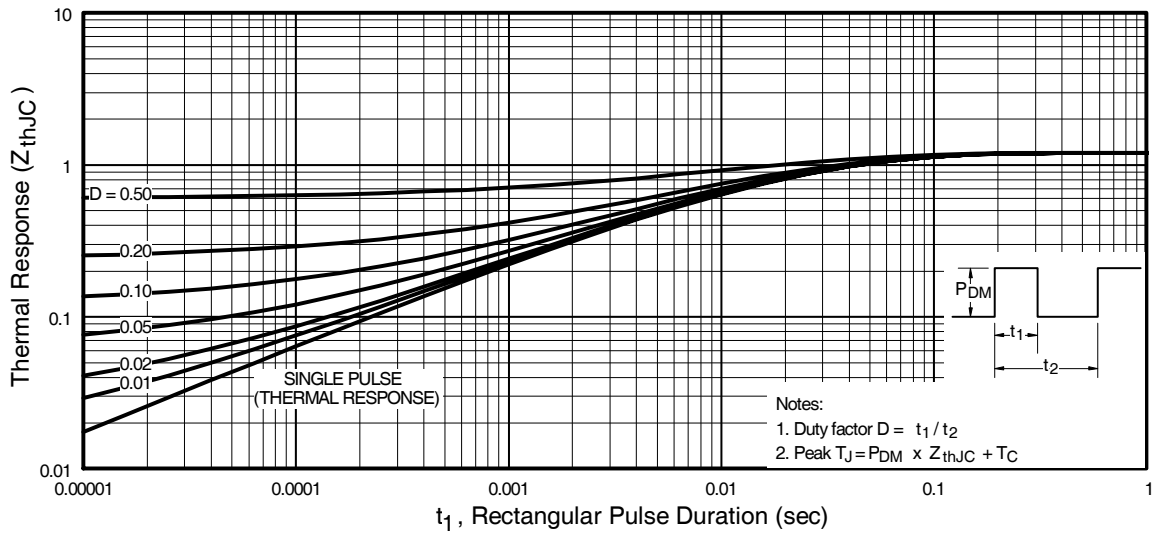


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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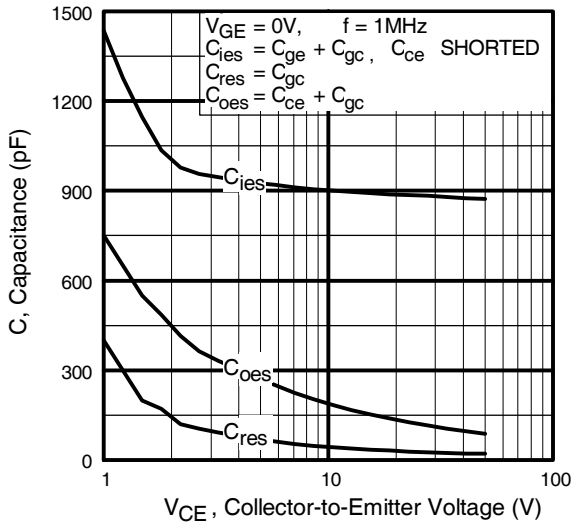


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

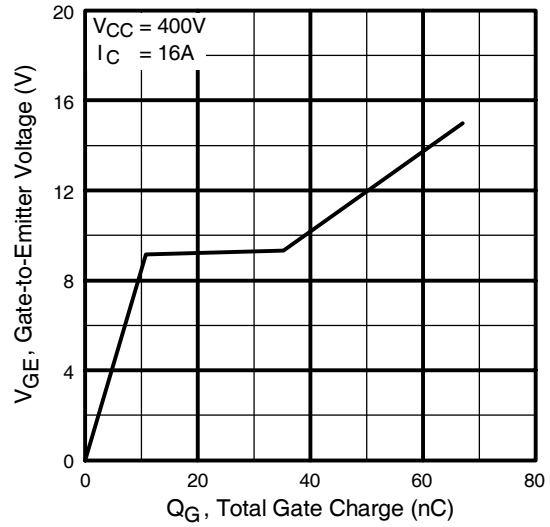


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

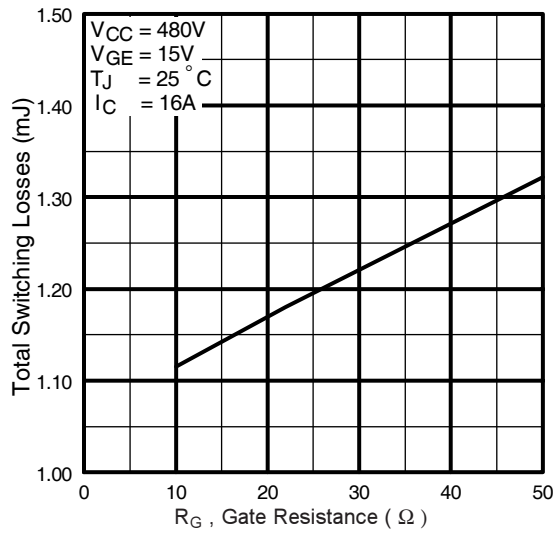


Fig. 9 - Typical Switching Losses vs. Gate Resistance

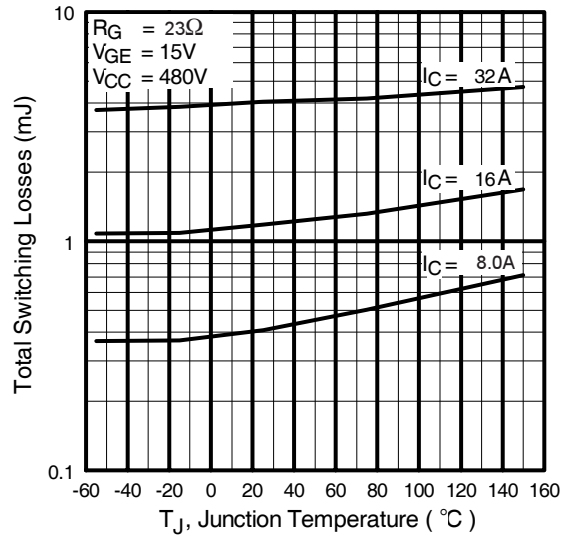


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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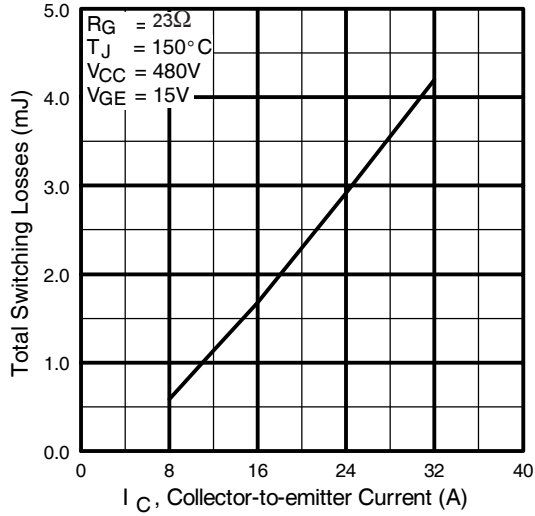


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

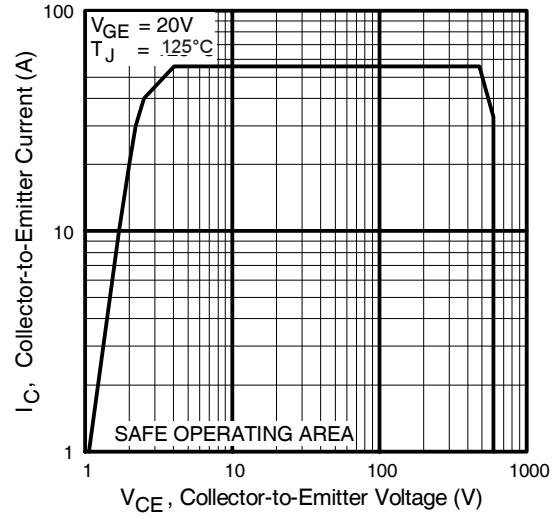


Fig. 12 - Turn-Off SOA

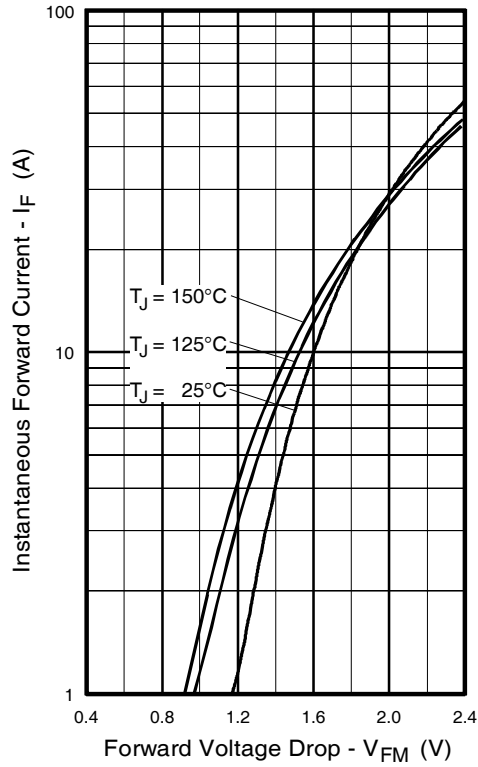


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

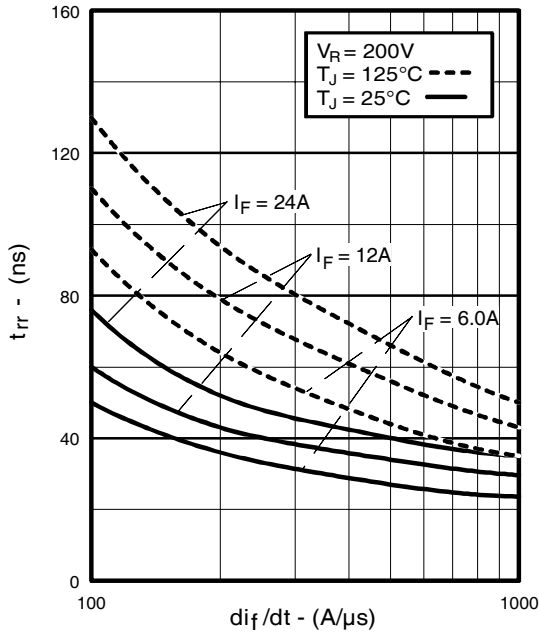


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

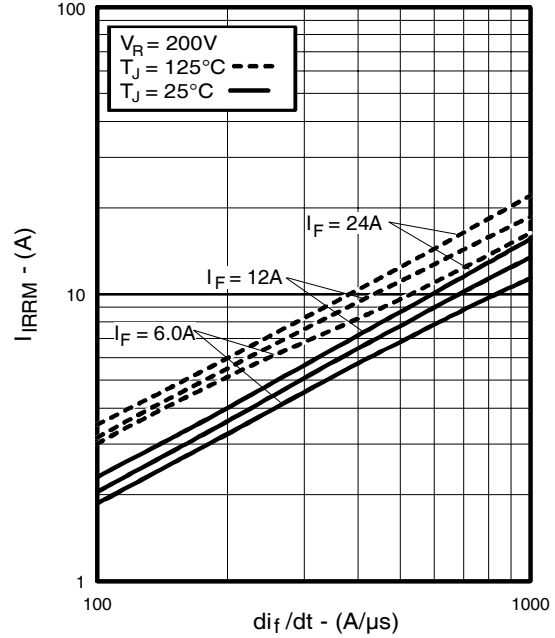


Fig. 15 - Typical Recovery Current vs. di_f/dt

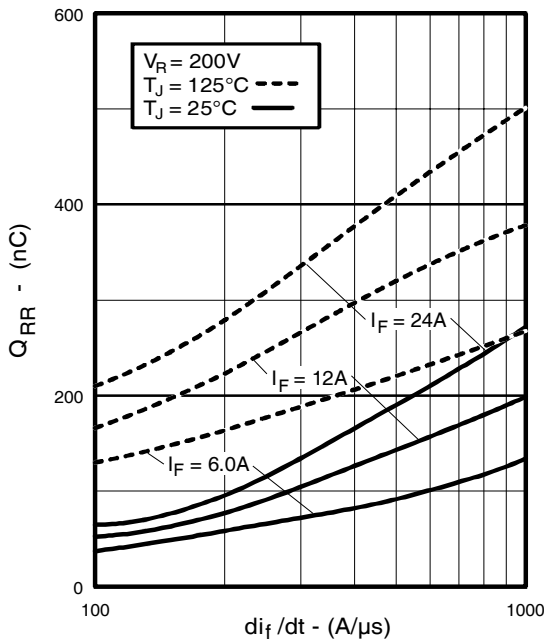


Fig. 16 - Typical Stored Charge vs. di_f/dt

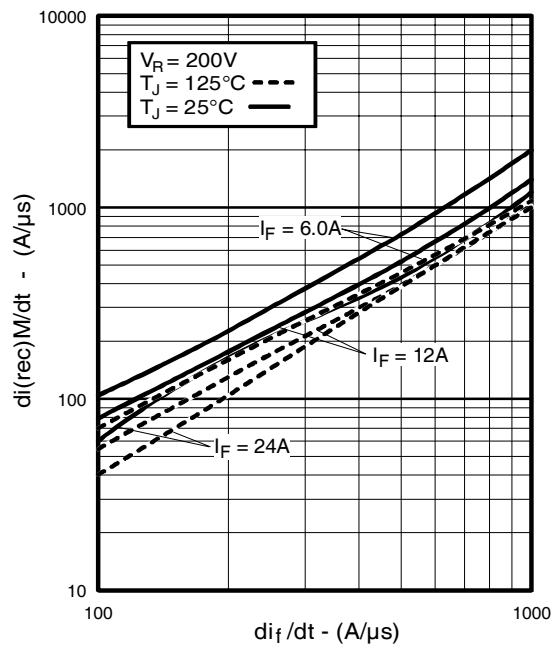


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

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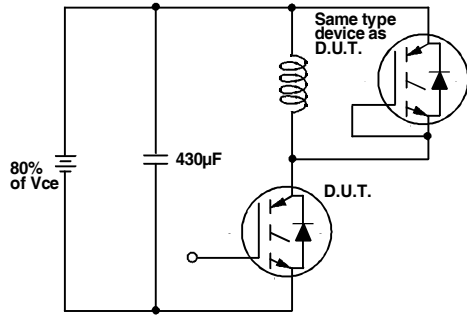


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

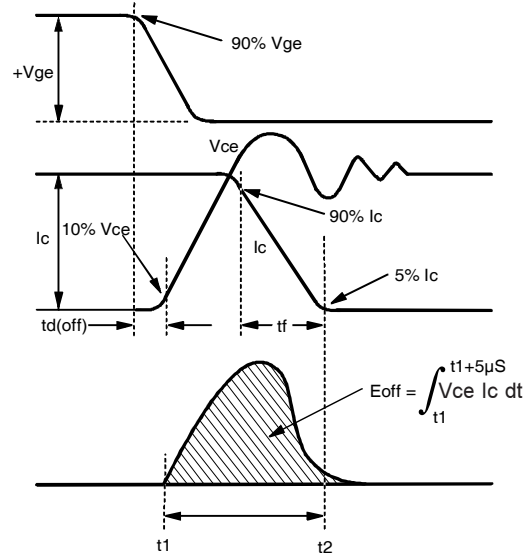


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

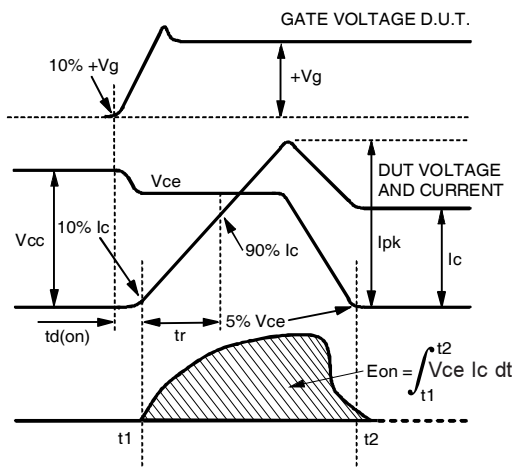


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

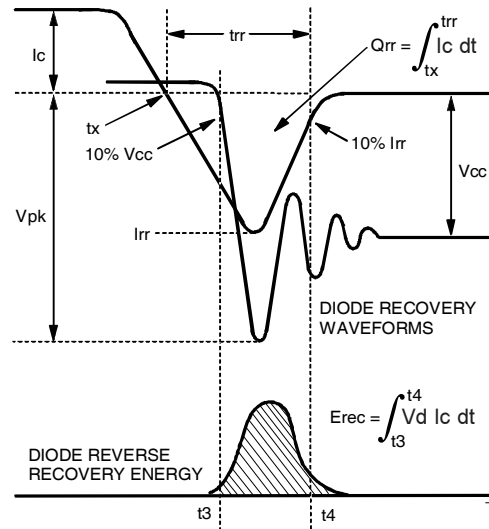


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

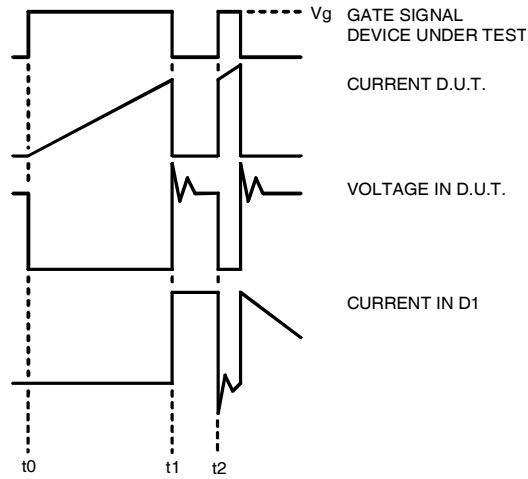


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

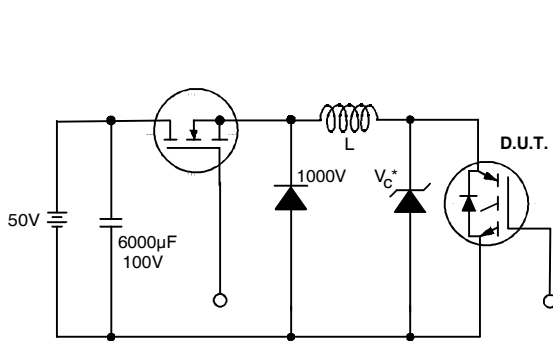


Figure 19. Clamped Inductive Load Test Circuit

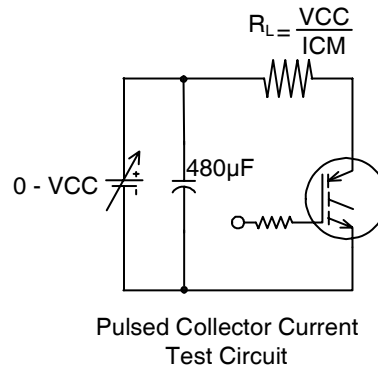


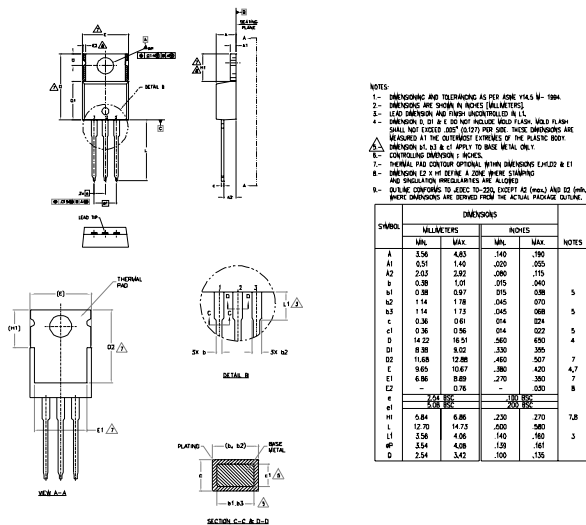
Figure 20. Pulsed Collector Current Test Circuit

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Notes:

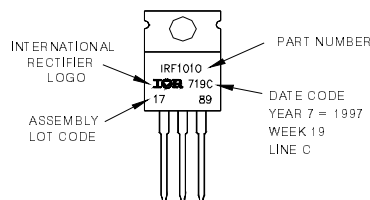
- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=23\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE 'C'
Note: "P" in assembly line position indicates "Lead-Free"



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.